

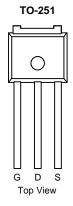
# 40N06B-VB TO251 Datasheet N-Channel 60 V (D-S) MOSFET

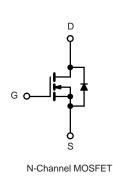
PRODUCT SUMMARY					
V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (A) <sup>a</sup>			
60	0.012at V <sub>GS</sub> = 10 V	55			
60	0.015 at V <sub>GS</sub> = 4.5 V	47			

### **FEATURES**

- 175 °C Junction Temperature
- Trench Power MOSFET
- Material categorization:







<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C, unless otherwise noted)						
Parameter	Symbol	Limit	Unit			
Gate-Source Voltage	$V_{GS}$	± 20	V			
Continuous Drain Current /T 175 9C\D	T <sub>C</sub> = 25 °C	I-	55			
Continuous Drain Current (T <sub>J</sub> = 175 °C) <sup>b</sup>	T <sub>C</sub> = 100 °C	- I <sub>D</sub>	46 <sup>a</sup>			
Pulsed Drain Current	I <sub>DM</sub>	110	A			
Continuous Source Current (Diode Conduction)	I <sub>S</sub>	50 <sup>a</sup>				
Avalanche Current		I <sub>AS</sub>	I <sub>AS</sub> 50			
Single Avalanche Energy (Duty Cycle ≤ 1 %)	L = 0.1 mH	E <sub>AS</sub>	125	mJ		
Maximum Power Dissipation	T <sub>C</sub> = 25 °C	P <sub>D</sub>	136	w		
Maximum Power Dissipation	T <sub>A</sub> = 25 °C	' D	3 <sup>b</sup> , 8.3 <sup>b, c</sup>	]		
Operating Junction and Storage Temperature Range	-	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 175	°C		

THERMAL RESISTANCE RATINGS							
Parameter		Symbol	Typical	Maximum	Unit		
Marian de Lucation to Ambienti	t ≤ 10 sec	R <sub>thJA</sub>	15	18	°C/W		
Maximum Junction-to-Ambient <sup>a</sup>	Steady State		40	50			
Maximum Junction-to-Case	•	R <sub>thJC</sub>	0.85	1.1			

#### Notes:

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- c.  $t \le 10$  s.

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Parameter	Symbol Test Conditions		Min.	Typ. <sup>a</sup>	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	60			V	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$			3		
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
		V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V	1		1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C			50	μΑ	
		V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 175 °C			250		
On-State Drain Current <sup>b</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = 5 V, V <sub>GS</sub> = 10 V	60			Α	
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A		0.012			
D : 0	D	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A, T <sub>J</sub> = 125 °C		0.013		Ω	
Drain-Source On-State Resistance <sup>b</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A, T <sub>J</sub> = 175 °C		0.017			
		$V_{GS} = 4.5 \text{ V}, I_D = 15 \text{ A}$		0.015			
Forward Transconductance <sup>b</sup>	9 <sub>fs</sub>	$V_{DS} = 15 \text{ V}, I_{D} = 20 \text{ A}$		60		S	
Dynamic			•				
Input Capacitance	C <sub>iss</sub>			3650		pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$		570			
Reverse Transfer Capacitance	C <sub>rss</sub>			325			
Total Gate Charge <sup>c</sup>	Qg			46			
Gate-Source Charge <sup>c</sup>	$Q_{gs}$	$V_{DS} = 30 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 50 \text{ A}$		10		nC	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			12			
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			10	20		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$ = 30 V, $R_L$ = 0.6 $\Omega$		15	25		
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 50 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 2.5 \Omega$		35	50	ns	
Fall Time <sup>c</sup>	t <sub>f</sub>			20	30		
Source-Drain Diode Ratings and Cha	aracteristics (	T <sub>C</sub> = 25 °C)		•			
Pulsed Current	I <sub>SM</sub>				60	Α	
Diode Forward Voltage	$V_{SD}$	I <sub>F</sub> = 20 A, V <sub>GS</sub> = 0 V		1	1.5	V	
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 20 A, di/dt = 100 A/μs		45	100	ns	

#### Notes:

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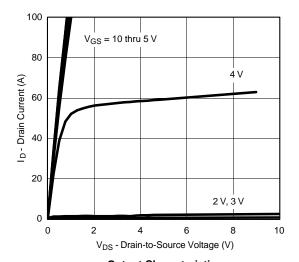
- a. For design aid only; not subject to production testing.
- b. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

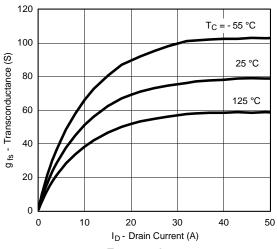
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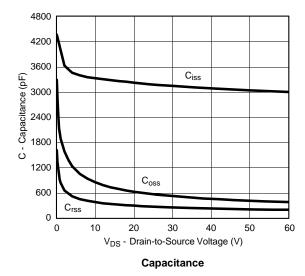
### TYPICAL CHARACTERISTICS (25 °C unless noted)

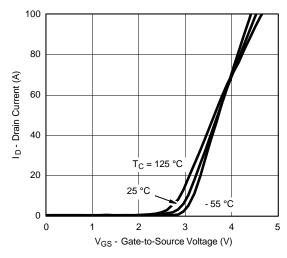


## **Output Characteristics**

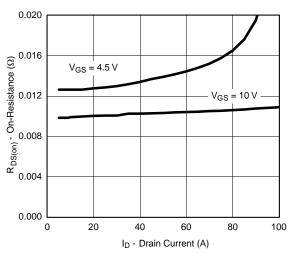


#### Transconductance

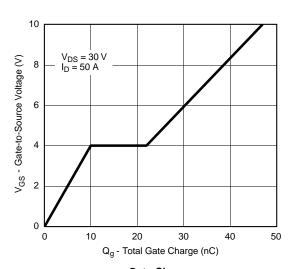




#### **Transfer Characteristics**



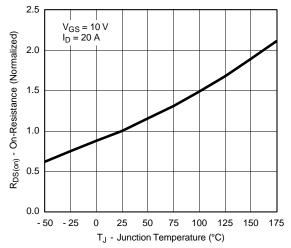
On-Resistance vs. Drain Current



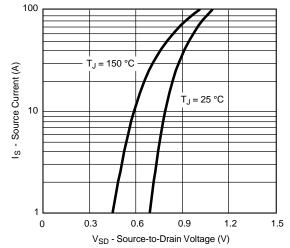
Gate Charge



## TYPICAL CHARACTERISTICS (25 °C unless noted)



On-Resistance vs. Junction Temperature

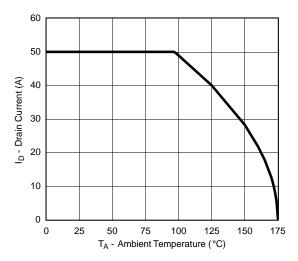


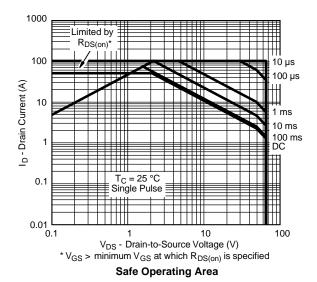
Source-Drain Diode Forward Voltage

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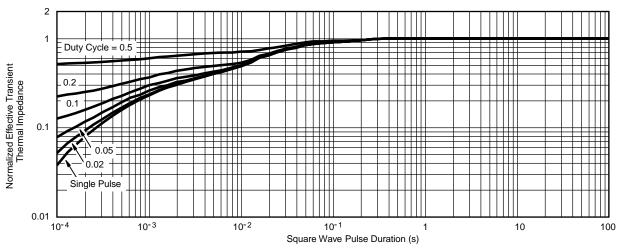


#### **THERMAL RATINGS**





Maximum Drain Current vs. Ambient Temperature



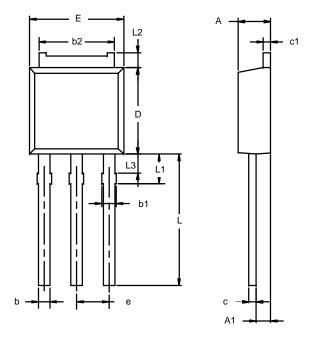
Normalized Thermal Transient Impedance, Junction-to-Case

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## TO-251AA (DPAK)



Note: Dimension L3 is for reference only.

	MILLIM	IETERS	INC	HES	
Dim	Min	Max	Min	Max	
Α	2.21	2.38	0.087	0.094	
A1	0.89	1.14	0.035	0.045	
b	0.71	0.89	0.028	0.035	
b1	0.76	1.14	0.030	0.045	
b2	5.23	5.43	0.206	0.214	
С	0.46	0.58	0.018	0.023	
с1	0.46	0.58	0.018	0.023	
D	5.97	6.22	0.235	0.245	
E	6.48	6.73	0.255	0.265	
е	2.28	BSC	0.090	BSC	
L	8.89	9.53	0.350	0.375	
L1	1.91	2.28	0.075	0.090	
L2	0.89	1.27	0.035	0.050	
L3	1.15	1.52	0.045	0.060	
ECN: S-03946—Rev. E, 09-Jul-01 DWG: 5346					

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